

■ PRODUCT CHARACTERISTICS

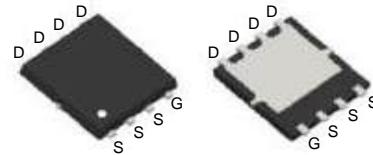
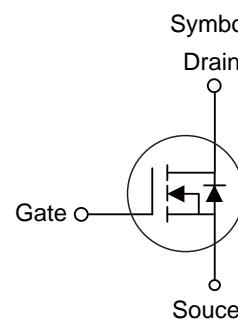
V _{DSS}	100V
R _{DSON} Typ(@V _{GS} =10V)	4.8mΩ
R _{DSON} Typ(@V _{GS} =4.5V)	7.5mΩ
I _D	90A

■ APPLICATIONS

- * Switching applications

■ FEATURES

- * Low capacitance
- * Low gate charge
- * Fast switching capability
- * Avalanche energy specified


■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT1148G	PDFN5X6-8L	5000 pieces/Reel

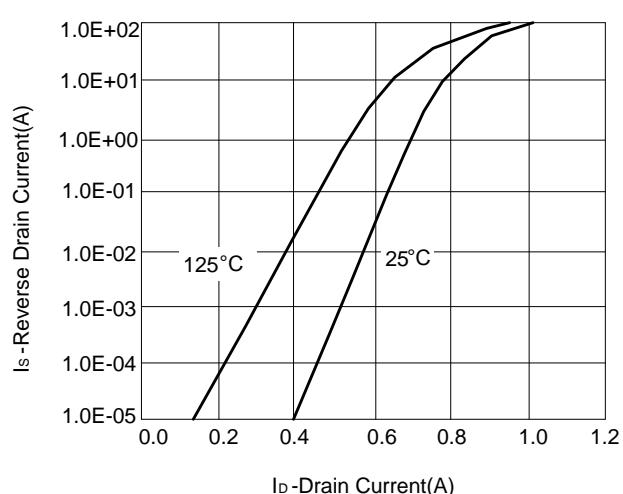
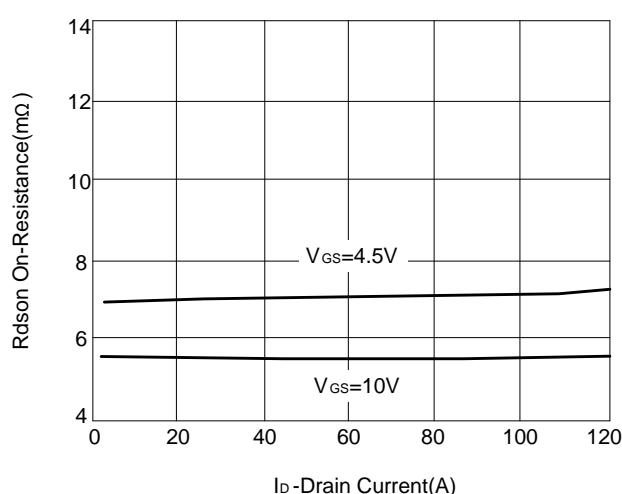
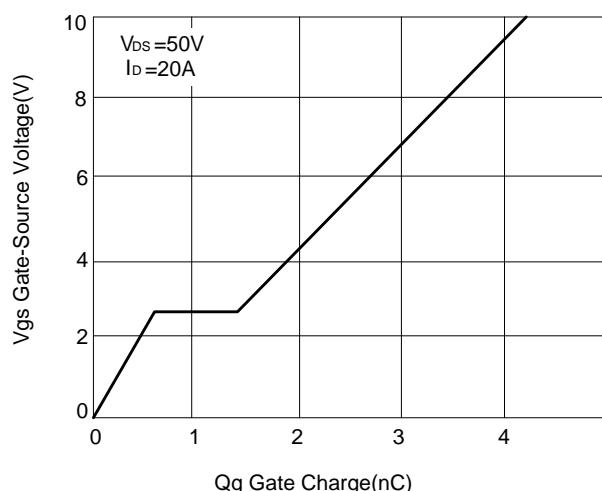
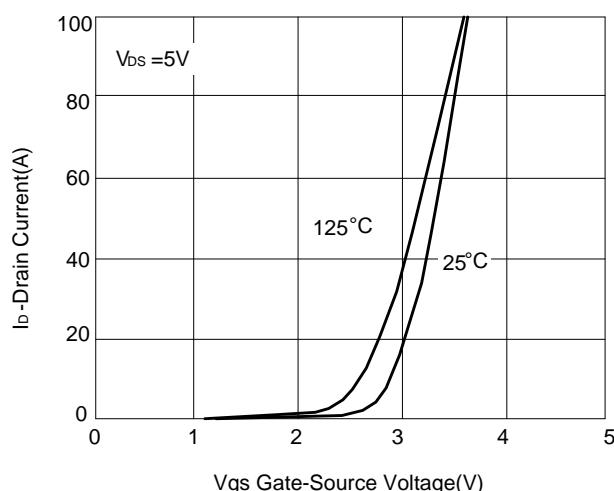
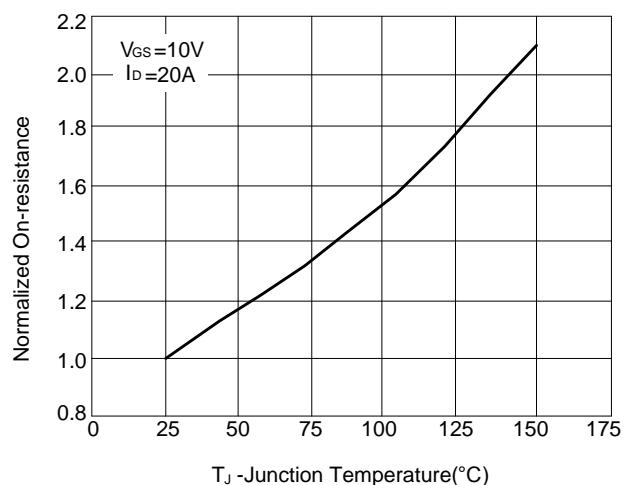
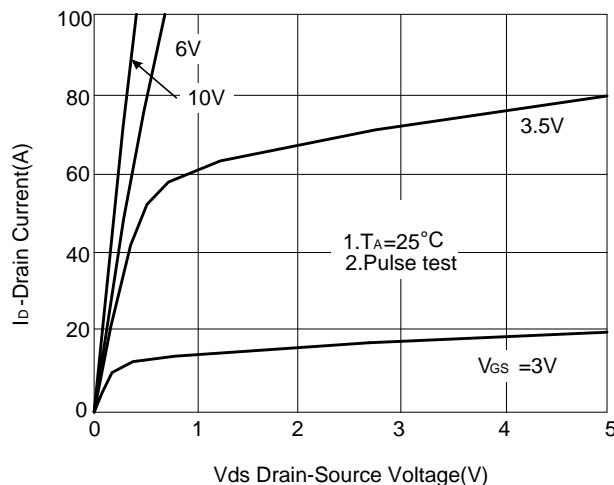
■ ABSOLUTE MAXIMUM RATINGS(T_A=25°C unless otherwise specified)

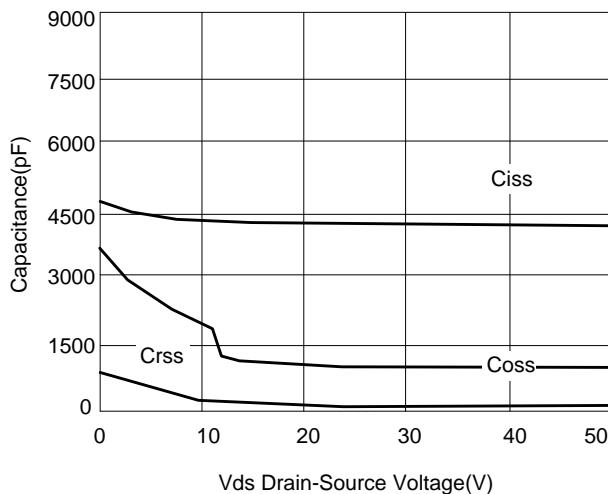
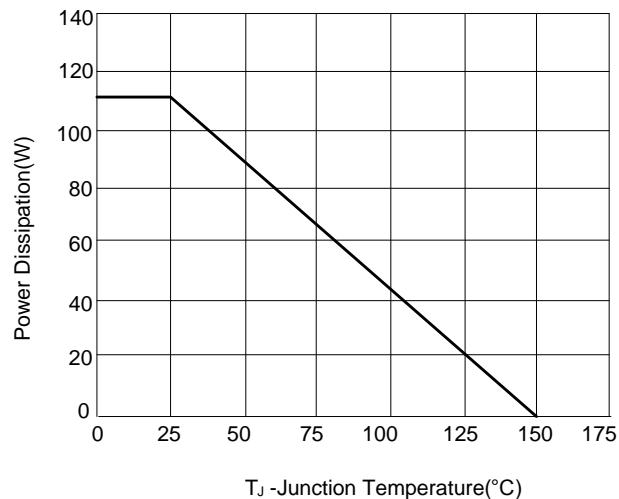
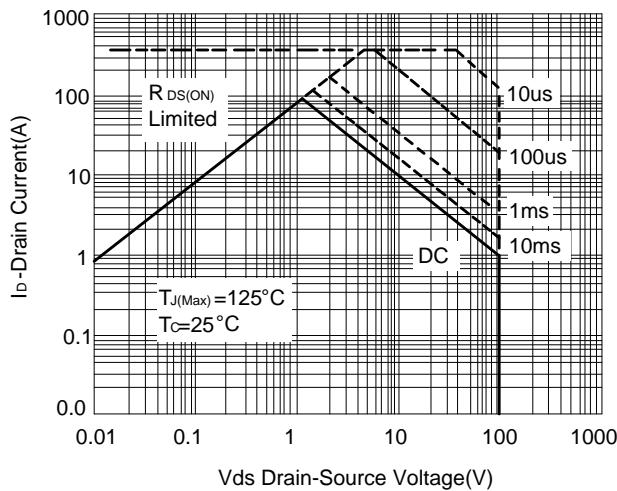
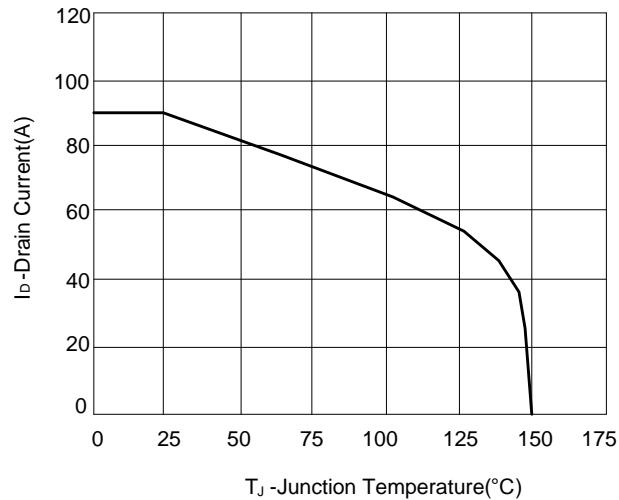
Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current@V _{GS} =10V	I _D	90	A
		65	A
Pulsed Drain Current	I _{DM}	360	A
Single Pulse Avalanche Energy	E _{AS}	420	mJ
Power Dissipation	P _D	110	W
Thermal Resistance,Junction to Case	R _{θJC}	1.14	°C/W
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55~+150	°C

■ ELECTRICAL CHARACTERISTICS($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100\text{V}, V_{GS}=0\text{V}$	-	-	1.0	μA
Gate to Body Leakage Current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$	-	-	± 100	nA
On characteristics						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.2	1.7	2.2	V
Static Drain-Source on-Resistance	$R_{DS(\text{on})}$	$V_{GS}=10\text{V}, I_D=20\text{A}$	-	4.8	6	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=20\text{A}$	-	7.5	8.6	$\text{m}\Omega$
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$ $f=1.0\text{MHz}$	-	3800	-	pF
Output Capacitance	C_{oss}		-	1200	-	pF
Reverse Transfer Capacitance	C_{rss}		-	98	-	pF
Total Gate Charge	Q_g	$V_{DS}=50\text{V}, I_D=20\text{A}$ $V_{GS}=10\text{V}$	-	83	-	nC
Gate-Source Charge	Q_{gs}		-	13	-	nC
Gate-Drain("Miller") Charge	Q_{gd}		-	15	-	nC
Switching characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=50\text{V}, I_D=20\text{A}$ $R_G=1.6\Omega, V_{GS}=10\text{V}$	-	17	-	ns
Turn-on Rise Time	t_r		-	10.5	-	ns
Turn-off Delay Time	$t_{d(off)}$		-	40	-	ns
Turn-off Fall Time	t_f		-	70	-	ns
Drain-source diode characteristics and maximum ratings						
Maximum Continuous forward Current	I_s		-	-	90	A
Maximum Pulsed forward Current	I_{SM}		-	-	360	A
Drain to Source Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}, I_s=3\text{A}$	-	0.73	0.99	V
Body Diode Reverse Recovery Time	t_{rr}	$I_s=45\text{A}$ $di/dt=100\text{A}/\mu\text{s}$	-	68	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	110	-	nC

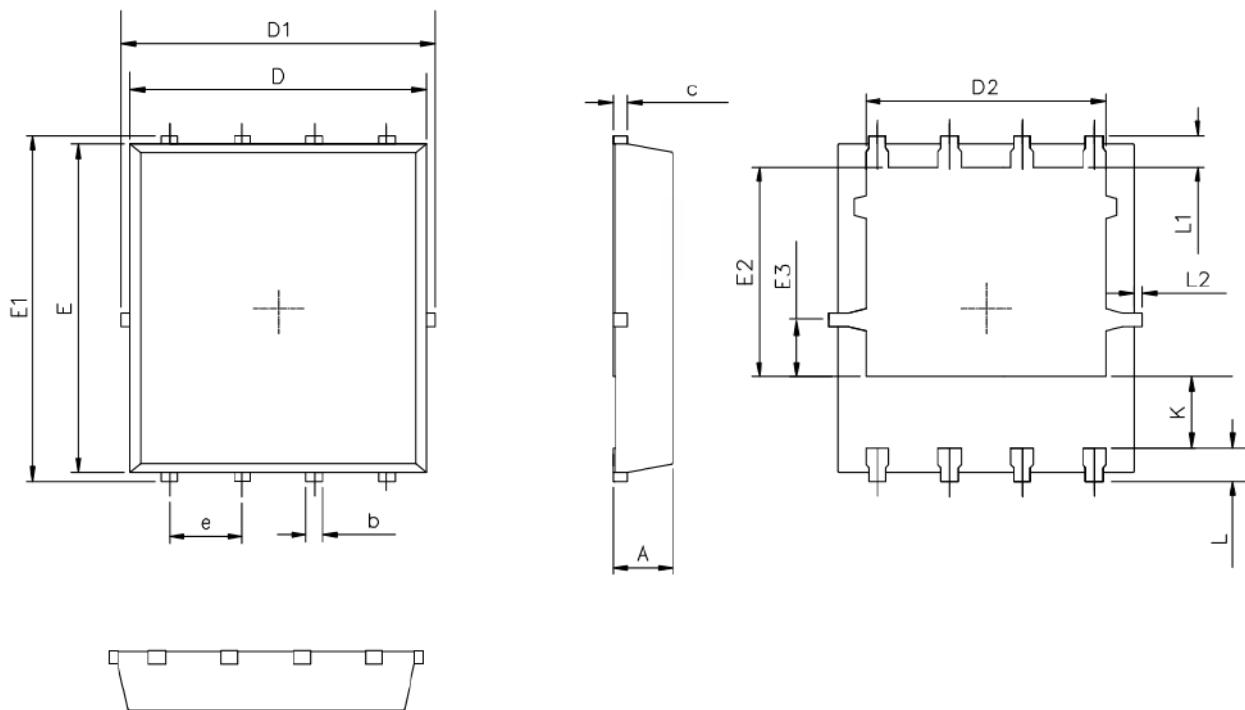
■ TYPICAL CHARACTERISTICS



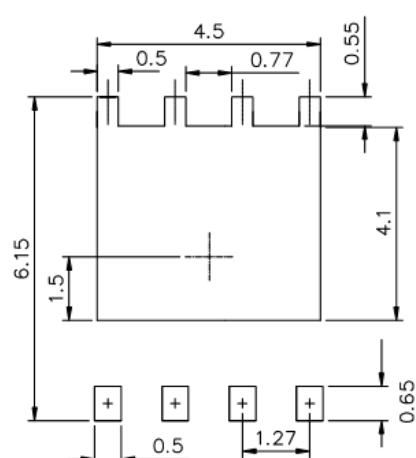
■ TYPICAL CHARACTERISTICS(Cont.)

Figure 7 Capacitance vs Vds

Figure 8 Power De-rating

Figure 9 Safe Operation Area

Figure 10 Current De-rating



■ PDFN5X6-8L Package Mechanical Date



RECOMMENDED LAND PATTERN



UNIT:mm

	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.25	0.35	0.50
c	0.10	0.20	0.30
D	4.80	5.00	5.30
D1	4.90	5.10	5.50
D2	3.92	4.02	4.20
E	5.65	5.75	5.85
E1	5.90	6.05	6.20
E2	3.325	3.525	3.775
E3	0.80	0.90	1.00
e		1.27	
L	0.40	0.55	0.70
L1		0.65	
L2	0.00		0.15
K	1.00	1.30	1.50